

N-P-N epitaxial planar transistor intended for use in class-A, B and C operated mobile, industrial and military transmitters with a supply voltage of 13,5 V. The transistor is resistance stabilized. Every transistor is tested under severe load mismatch conditions with a supply over-voltage to 16,5 V. It has a ¼" capstan envelope with a moulded cap. All leads are isolated from the stud.

### QUICK REFERENCE DATA

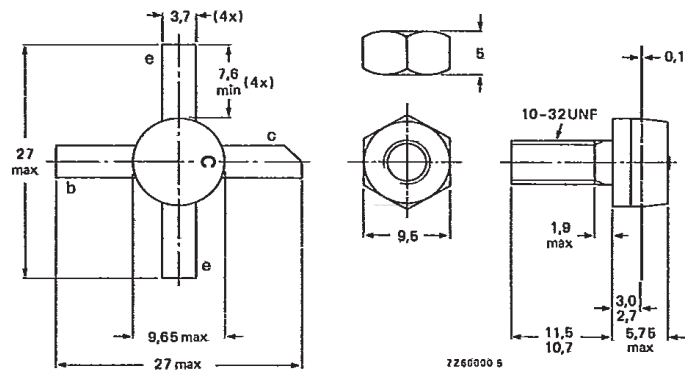
R.F. performance up to  $T_{mb} = 25\text{ }^{\circ}\text{C}$  in an unneutralized common-emitter class-B circuit

mode of operation	$V_{CE}$ V	f MHz	$P_S$ W	$P_L$ W	$I_C$ A	$G_p$ dB	$\eta$ %	$\bar{z}_i$ $\Omega$	$\bar{Y}_L$ mS
c.w.	13,5	175	< 6,25	25	< 2,64	> 6	> 70	$1,6 + j1,4$	$213 + j5,5$

### MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-56.



### RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) peak value	$V_{CBOM}$	max.	36	V
Collector-emitter voltage (open base)	$V_{CEO}$	max.	18	V
Emitter-base voltage (open collector)	$V_{EBO}$	max.	4	V
Collector current (average)	$I_{C(AV)}$	max.	5	A
Collector current (peak value) $f > 1\text{ MHz}$	$I_{CM}$	max.	10	A
Total power dissipation up to $T_{mb} = 25\text{ }^{\circ}\text{C}$ $f > 1\text{ MHz}$	$P_{tot}$	max.	70	W

Note : Above parameters , ratings , limits and conditions are subject to change .